

# WESTCODE



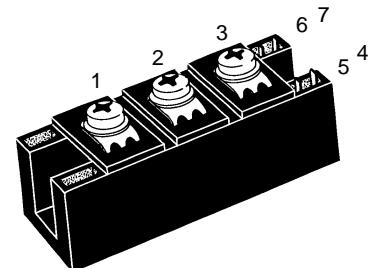
## SEMICONDUCTORS

### Thyristor Modules Thyristor/Diode Modules

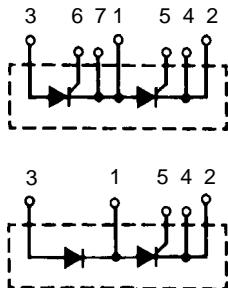
**I<sub>TRMS</sub>** = 2 x 300 A  
**I<sub>TAVM</sub>** = 2 x 190 A  
**V<sub>RRM</sub>** = 800 - 1800 V

V <sub>RSM</sub>	V <sub>RRM</sub>	Type
V <sub>DSM</sub>	V <sub>DRM</sub>	
V	V	
900	800	WPT 162-08
1300	1200	WPT 162-12
1500	1400	WPT 162-14
1700	1600	WPT 162-16
1900	1800	WPT 162-18

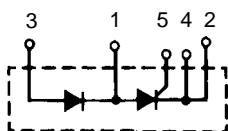
Symbol	Test Conditions	Maximum Ratings		
I <sub>TRMS</sub> , I <sub>FRMS</sub>	T <sub>VJ</sub> = T <sub>VJM</sub>	300	A	
I <sub>TAVM</sub> , I <sub>FAVM</sub>	T <sub>C</sub> = 80°C; 180° sine	190	A	
	T <sub>C</sub> = 85°C; 180° sine	181	A	
I <sub>TSM</sub> , I <sub>FSM</sub>	T <sub>VJ</sub> = 45°C; V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	6000 6400	A A
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	5250 5600	A A
j <sup>2</sup> dt	T <sub>VJ</sub> = 45°C V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	180 000 170 000	A <sup>2</sup> s A <sup>2</sup> s
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	137 000 128 000	A <sup>2</sup> s A <sup>2</sup> s
(di/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> f = 50 Hz, t <sub>p</sub> = 200 µs V <sub>D</sub> = 2/3 V <sub>DRM</sub> I <sub>G</sub> = 0.5 A di <sub>G</sub> /dt = 0.5 A/µs	repetitive, I <sub>T</sub> = 500 A non repetitive, I <sub>T</sub> = 500 A	150 500	A/µs A/µs
(dv/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> ; R <sub>GK</sub> = ∞; method 1 (linear voltage rise)	V <sub>DR</sub> = 2/3 V <sub>DRM</sub>	1000	V/µs
P <sub>GM</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> I <sub>T</sub> = I <sub>TAVM</sub>	t <sub>p</sub> = 30 µs t <sub>p</sub> = 500 µs	120 60 8	W W W
P <sub>GAV</sub>				V
V <sub>RGM</sub>			10	V
T <sub>VJ</sub>			-40...+125	°C
T <sub>VJM</sub>			125	°C
T <sub>stg</sub>			-40...+125	°C
V <sub>ISOL</sub>	50/60 Hz, RMS I <sub>ISOL</sub> ≤ 1 mA	t = 1 min t = 1 s	3000 3600	V~
M <sub>d</sub>	Mounting torque (M6) Terminal connection torque (M6)		2.25-2.75/20-25 Nm/lb.in. 4.5-5.5/40-48 Nm/lb.in.	
Weight	Typical including screws		125	g



WPT 162



WPH 162



#### Features

- International standard package
- Direct copper bonded Al<sub>2</sub>O<sub>3</sub>-ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- Keyed gate/cathode twin pins

#### Applications

- Motor control
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Contactless switches

#### Advantages

- Space and weight savings
- Simple mounting
- Improved temperature and power cycling
- Reduced protection circuits

Symbol	Test Conditions	Characteristic Values		
$I_{RRM}, I_{DRM}$	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	10	mA	
$V_T, V_F$	$I_T, I_F = 300 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.25	V	
$V_{TO}$	For power-loss calculations only ( $T_{VJ} = 125^\circ\text{C}$ )	0.88	V	
$r_T$		1.15	$\text{m}\Omega$	
$V_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	2.5	V	
$I_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	150	mA	
		200	mA	
$V_{GD}$	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	0.2	V	
$I_{GD}$		10	mA	
$I_L$	$T_{VJ} = 25^\circ\text{C}; t_p = 30 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.5 \text{ A}; di_G/dt = 0.5 \text{ A}/\mu\text{s}$	300	mA	
$I_H$	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	200	mA	
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.5 \text{ A}; di_G/dt = 0.5 \text{ A}/\mu\text{s}$	2	$\mu\text{s}$	
$t_q$	$T_{VJ} = T_{VJM}; I_T = 300 \text{ A}, t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	$\mu\text{s}$	
$Q_s$	$T_{VJ} = T_{VJM}; I_T, I_F = 300 \text{ A}, -di/dt = 50 \text{ A}/\mu\text{s}$	550	$\mu\text{C}$	
$I_{RM}$		235	A	
$R_{thJC}$	per thyristor/diode; DC current	other values see Fig. 8/9	0.155	K/W
	per module		0.0775	K/W
$R_{thJK}$	per thyristor/diode; DC current		0.225	K/W
	per module		0.1125	K/W
$d_s$	Creepage distance on surface	12.7	mm	
$d_A$	Strike distance through air	9.6	mm	
$a$	Maximum allowable acceleration	50	$\text{m}/\text{s}^2$	

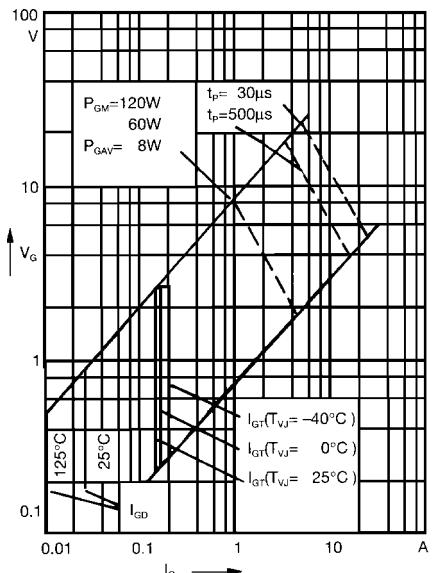


Fig. 1 Gate trigger characteristics

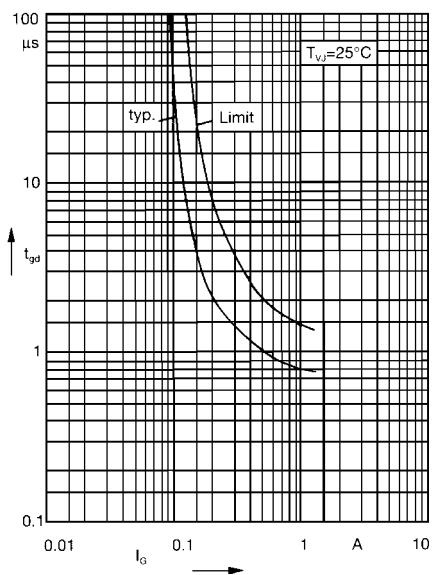
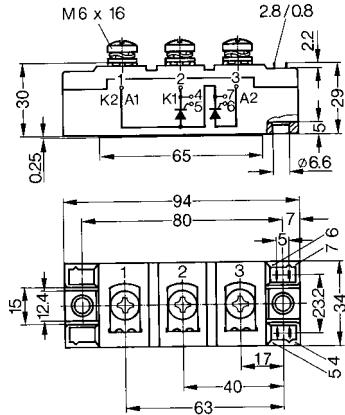


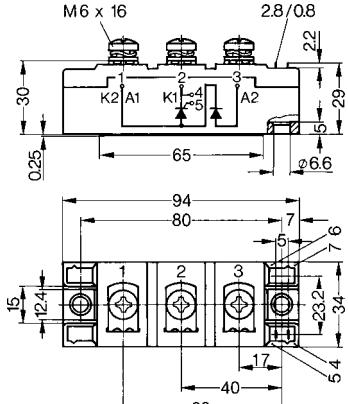
Fig. 2 Gate trigger delay time

**Dimensions in mm (1 mm = 0.0394")**

WPT 162



WPH 162



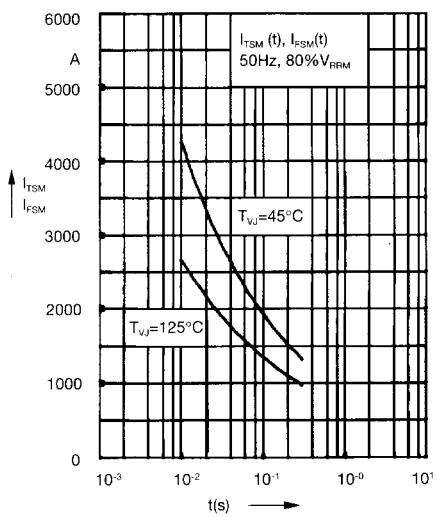


Fig. 3 Surge overload current  
 $I_{TSM}, I_{FSM}$ : Crest value,  $t$ : duration

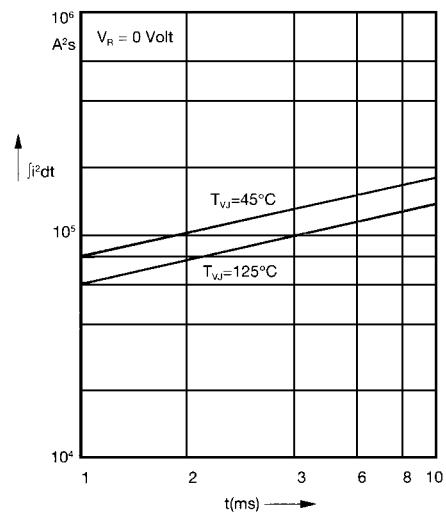


Fig. 4  $\int i^2 dt$  versus time (1-10 ms)

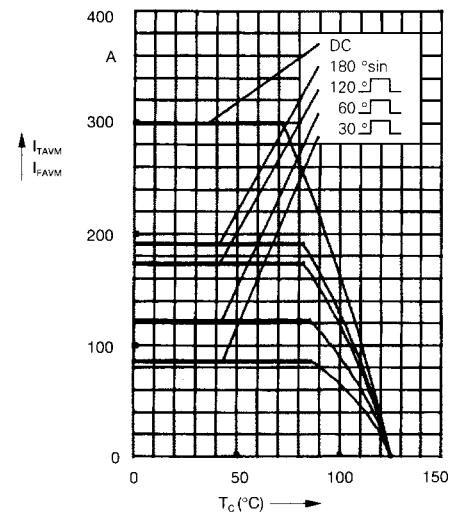


Fig. 4a Maximum forward current  
at case temperature

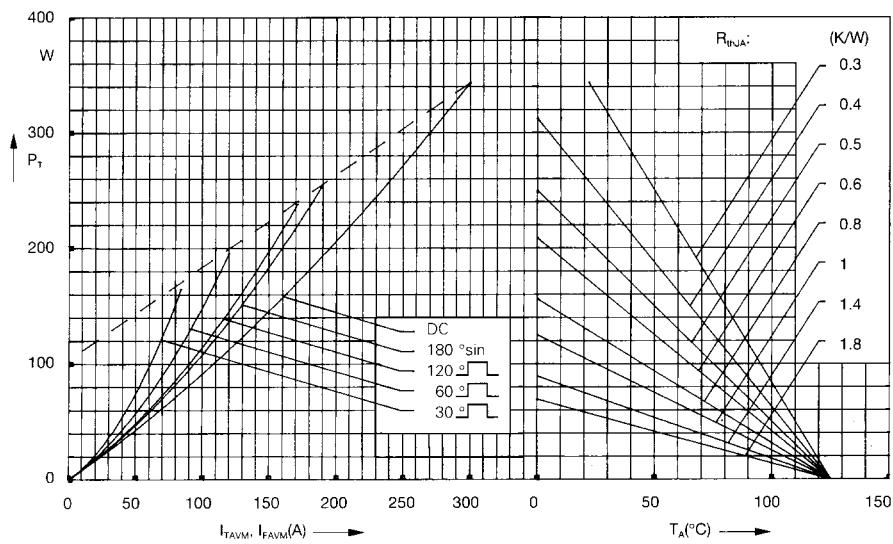


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

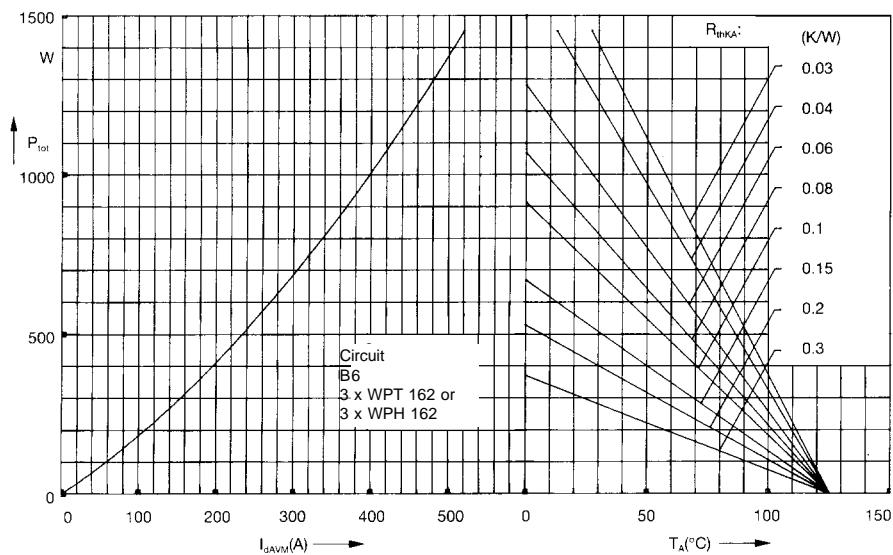


Fig. 6 Three phase rectifier bridge:  
Power dissipation versus direct output current and ambient temperature

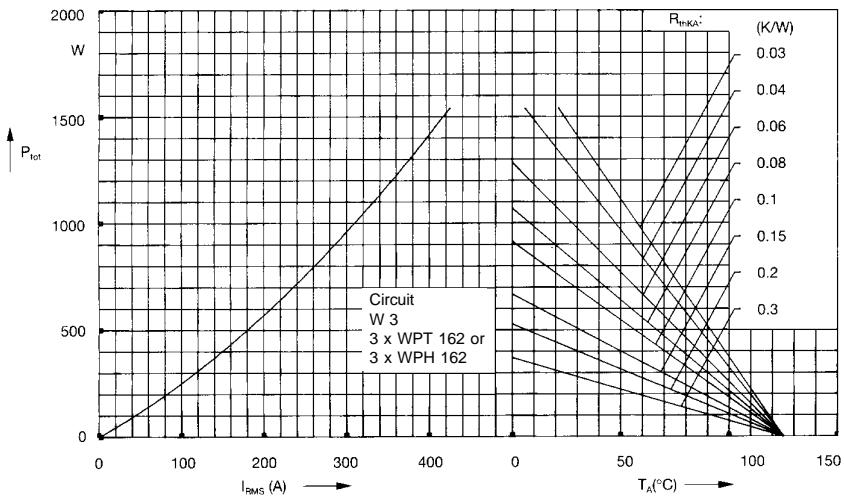


Fig. 7 Three phase AC-controller:  
Power dissipation versus RMS  
output current and ambient  
temperature

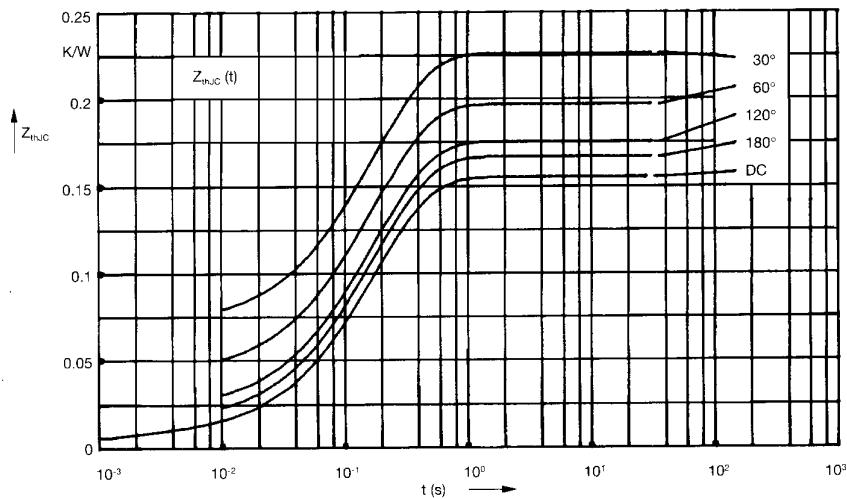


Fig. 8 Transient thermal impedance junction  
to case (per thyristor or diode)

$R_{thJC}$  for various conduction angles d:

d	$R_{thJC}$ (K/W)
DC	0.155
180°	0.167
120°	0.176
60°	0.197
30°	0.227

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.0072	0.001
2	0.0188	0.08
3	0.129	0.2

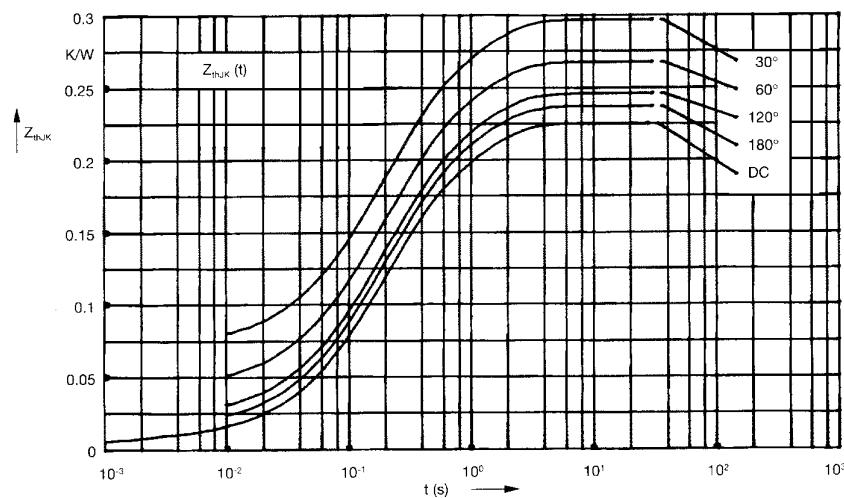


Fig. 9 Transient thermal impedance junction  
to heatsink (per thyristor or diode)

$R_{thJK}$  for various conduction angles d:

d	$R_{thJK}$ (K/W)
DC	0.225
180°	0.237
120°	0.246
60°	0.267
30°	0.297

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.0072	0.001
2	0.0188	0.08
3	0.129	0.2
4	0.07	1.0

**WESTCODE**   
SEMICONDUCTORS

WWW: <http://www.westcode.com>

In the interest of Product improvement Westcode reserves the right to change specifications at any time without notice.

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